

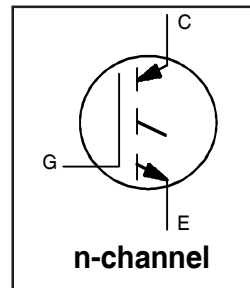
IRG4PH50S-EPbF

INSULATED GATE BIPOLAR TRANSISTOR

Standard Speed IGBT

Features

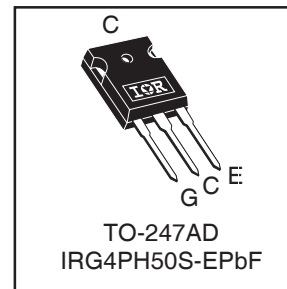
- Standard: Optimized for minimum saturation voltage and low operating frequencies (< 1kHz)
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- Industry standard TO-247AC package
- Lead-Free



$V_{CES} = 1200V$
$V_{CE(on)} \text{ typ.} = 1.47V$
@ $V_{GE} = 15V, I_C = 33A$

Benefits

- Generation 4 IGBT's offer highest efficiency available
- IGBT's optimized for specified application conditions
- Designed to be a "drop-in" replacement for equivalent industry-standard Generation 3 IR IGBT's



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	57	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	33	
I_{CM}	Pulsed Collector Current ^①	114	
I_{LM}	Clamped Inductive Load Current ^②	114	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
	Transient Gate-to-Emitter Voltage	± 30	
E_{ARV}	Reverse Voltage Avalanche Energy ^③	270	mJ
$P_D @ T_C = 25^\circ$	Maximum Power Dissipation	200	W
$P_D @ T_C = 100^\circ$	Maximum Power Dissipation	80	
T_J	Operating Junction and	-55 to + 150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf·in (1.1 N·m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	0.64	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	40	
Wt	Weight	—	6.0(0.21)	—	g (oz)

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0 A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	1.22	—	V/°C	$V_{GE} = 0V, I_C = 2.0 mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	1.47	1.7	V	$I_C = 33A, V_{GE} = 15V$
		—	1.75	—		$I_C = 57A, T_J = 150^\circ\text{C}$ See Fig.2, 5
		—	1.55	—		$I_C = 33A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$DV_{GE(th)}/DT_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ⑤	27	40	—	S	$V_{CE} = 100V, I_C = 33A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 1200V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 1200V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	167	251	nC	$I_C = 33A$ $V_{CC} = 400V$ See Fig. 8 $V_{GE} = 15V$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	25	38		
Q_{gc}	Gate - Collector Charge (turn-on)	—	55	83		
$t_{d(on)}$	Turn-On Delay Time	—	32	—	ns	$T_J = 25^{\circ}C$ $I_C = 33A, V_{CC} = 960V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail" See Fig. 9, 10, 14
t_r	Rise Time	—	29	—		
$t_{d(off)}$	Turn-Off Delay Time	—	845	1268		
t_f	Fall Time	—	425	638		
E_{on}	Turn-On Switching Loss	—	1.80	—	mJ	
E_{off}	Turn-Off Switching Loss	—	19.6	—		
E_{ts}	Total Switching Loss	—	21.4	44		
$t_{d(on)}$	Turn-On Delay Time	—	32	—	ns	$T_J = 150^{\circ}C$, $I_C = 33A, V_{CC} = 960V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail" See Fig. 10,11,14
t_r	Rise Time	—	30	—		
$t_{d(off)}$	Turn-Off Delay Time	—	1170	—		
t_f	Fall Time	—	1000	—		
E_{ts}	Total Switching Loss	—	37	—	mJ	
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	3600	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ See Fig. 7 $f = 1.0MHz$
C_{oes}	Output Capacitance	—	160	—		
C_{res}	Reverse Transfer Capacitance	—	30	—		

Notes:

- ① Repetitive rating; $V_{GE} = 20V$, pulse width limited by max. junction temperature. (See fig. 13b)
- ② $V_{CC} = 80\%(V_{CES})$, $V_{GE} = 20V$, $L = 10\mu H$, $R_G = 5.0\Omega$, (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ⑤ Pulse width $5.0\mu s$, single shot.

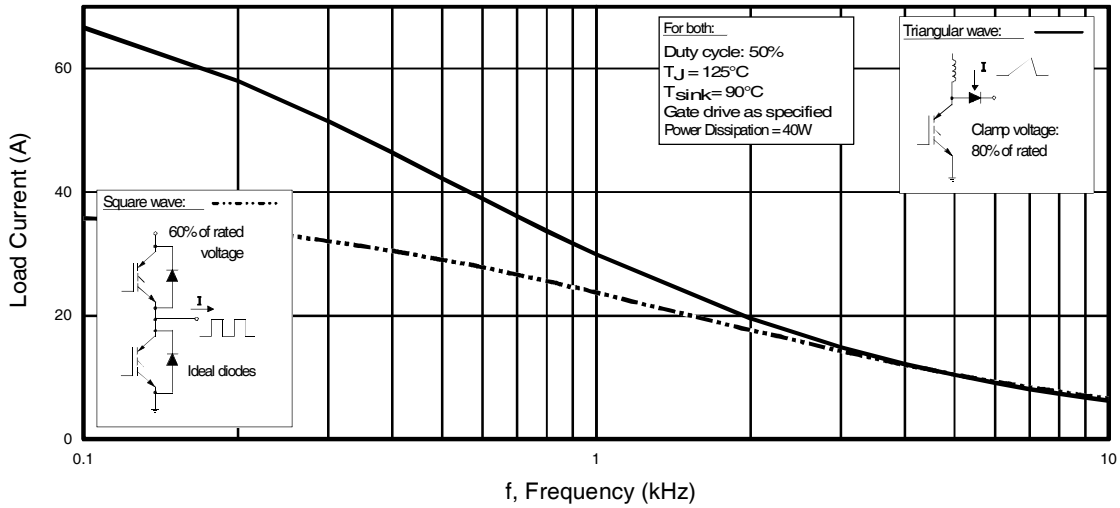


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

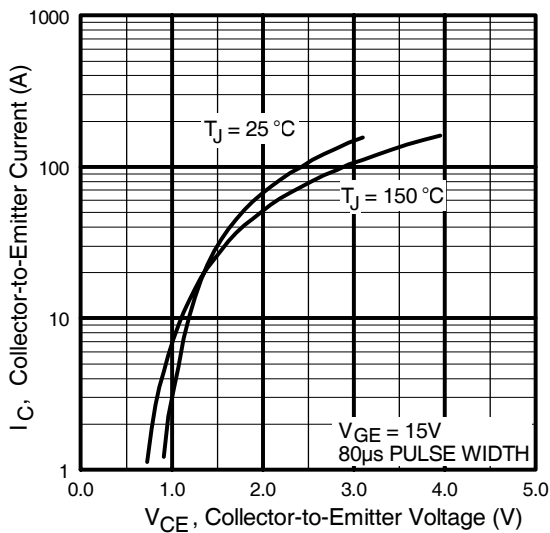


Fig. 2 - Typical Output Characteristics

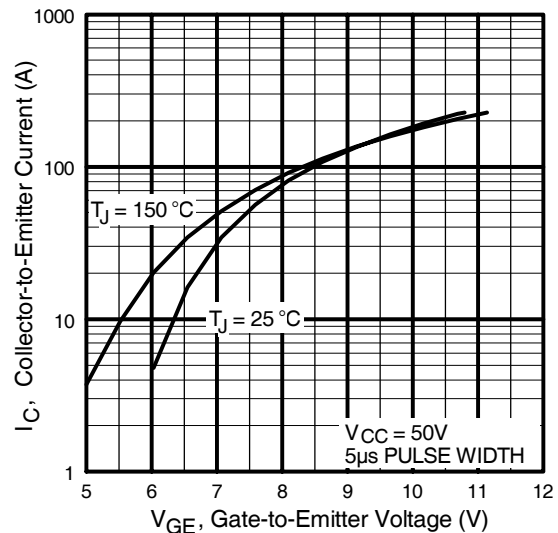


Fig. 3 - Typical Transfer Characteristics

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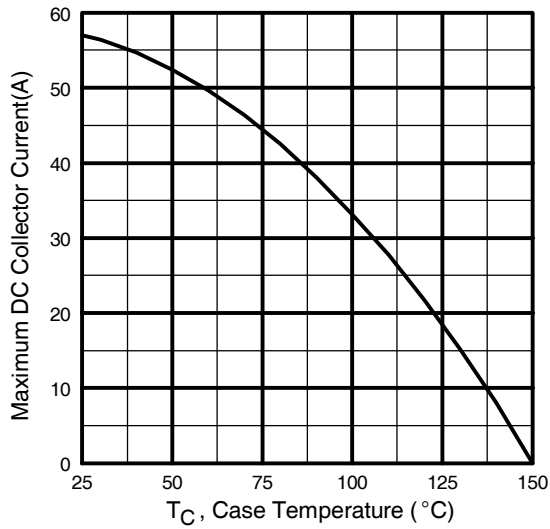


Fig. 4 - Maximum Collector Current vs. Case Temperature

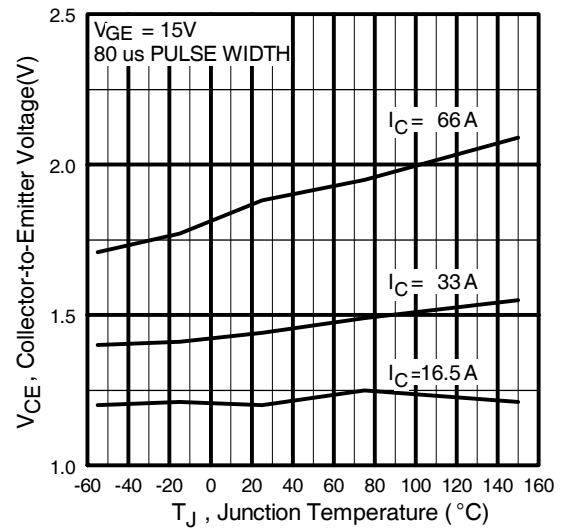


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

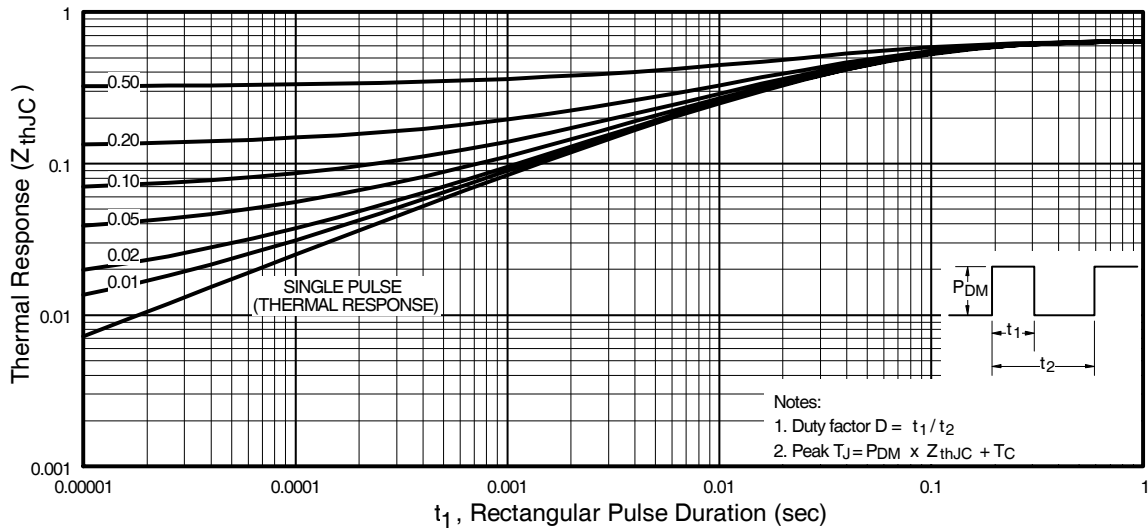


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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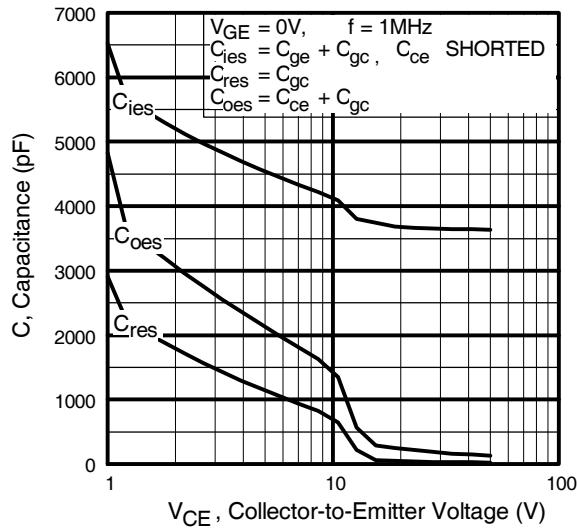


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

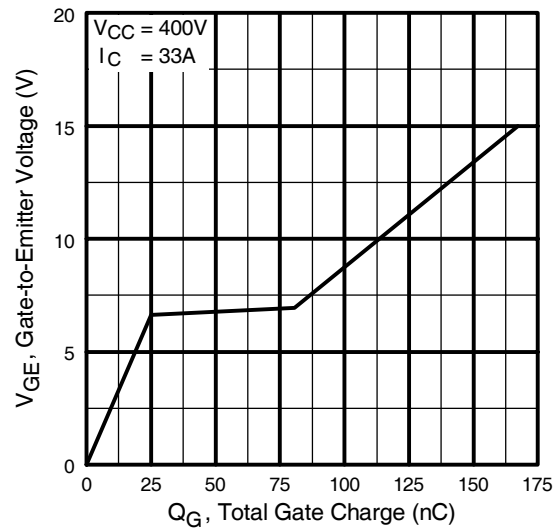


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

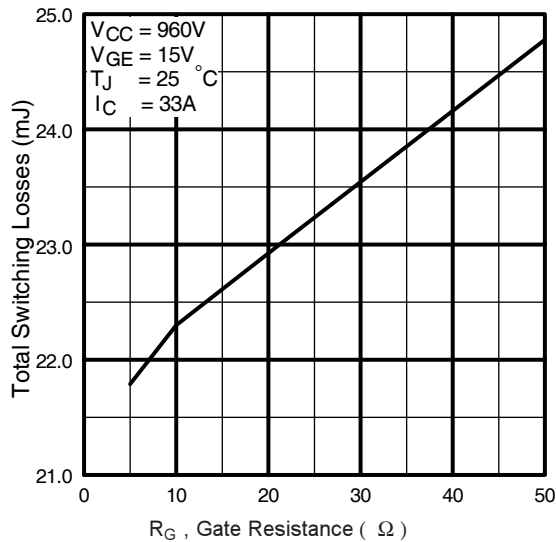


Fig. 9 - Typical Switching Losses vs. Gate Resistance

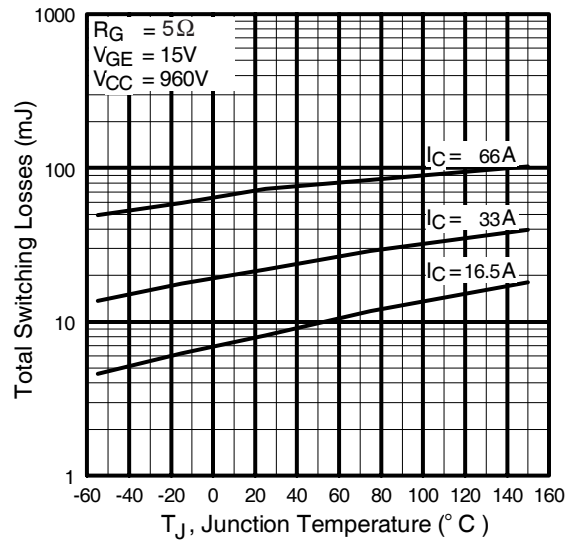


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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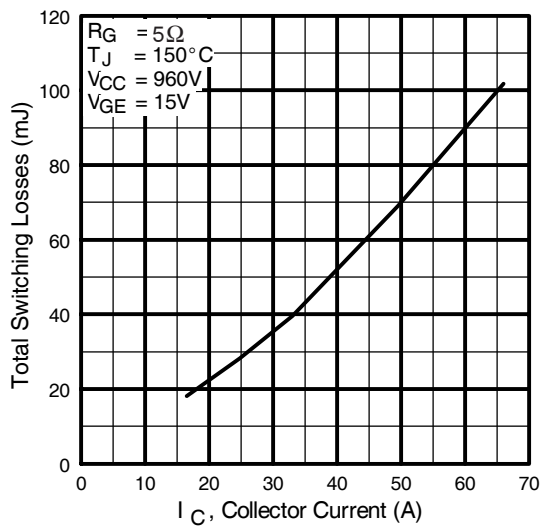


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

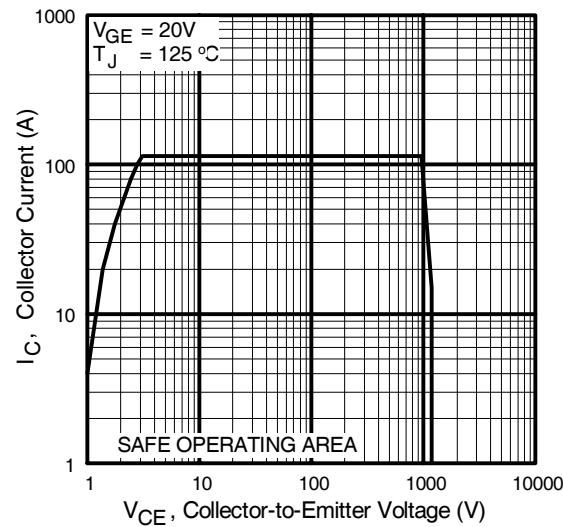


Fig. 12 - Reverse Bias SOA

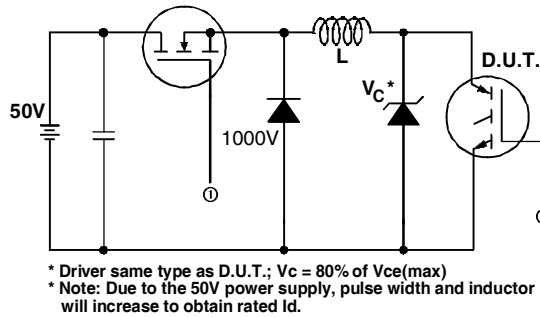


Fig. 13a - Clamped Inductive Load Test Circuit

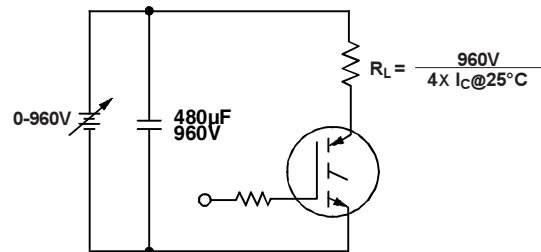


Fig. 13b - Pulsed Collector Current Test Circuit

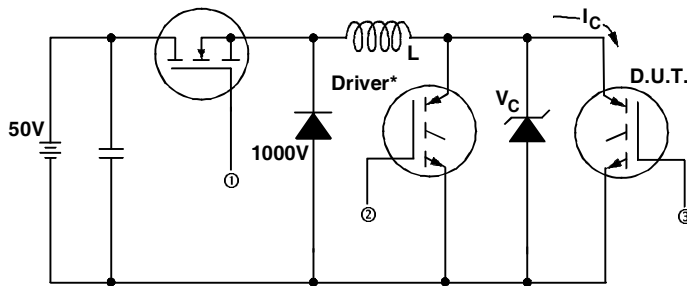


Fig. 14a - Switching Loss Test Circuit

* Driver same type as D.U.T., $V_C = \text{---}V$

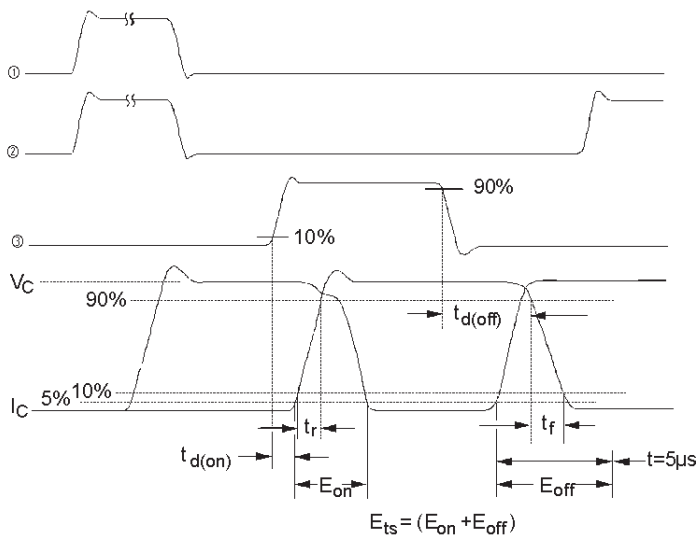
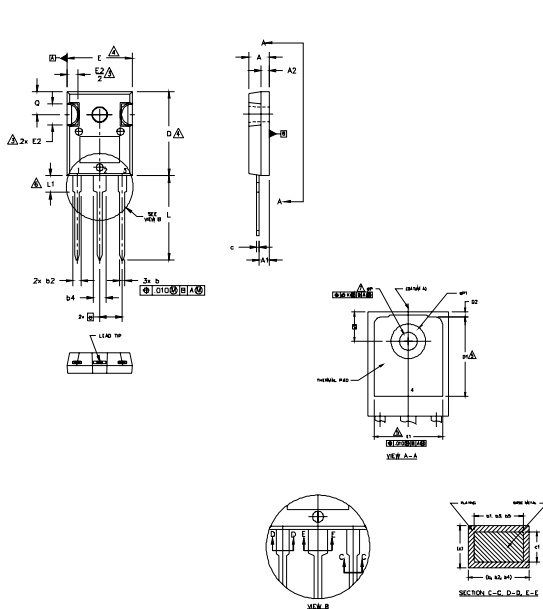


Fig. 14b - Switching Loss Waveforms

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TO-247AD Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AD.

SYMBOL	DIMENSIONS				NOTE
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.065	.99	1.40	
b1	.039	.053	.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	—	13.08	—	5
D2	.020	.063	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	—	13.46	—	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
Øk	.010		0.25		
L	.780	.827	19.57	21.00	
L1	.146	.169	3.71	4.29	
L2	.140	.144	3.56	3.66	
ØP1	—	.291	—	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

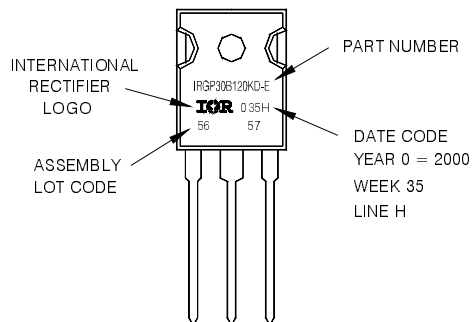
DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

TO-247AD Part Marking Information

EXAMPLE: THIS IS AN IRGP30B120KD-E
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2000
IN THE ASSEMBLY LINE 'H'

Note: 'P' in assembly line position
indicates 'Lead-Free'



TO-247AD package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Data and specifications subject to change without notice.

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